MICROWAVE POWER GaAs FET

Features

- Low intermodulation distortion
- IM₃ = -45 dBc at Po = 29.0 dBm, Single Carrier Level
- High power
 - P_{1dB} = 40.5 dBm at 14.0 GHz to 14.5 GHz
- High gain
- G_{1dB} = 6.0 dB at 14.0 GHz to 14.5 GHz
- Broadband internally matched
- Hermetically sealed package

RF Performance Specifications (T_a = 25°C)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max.	
Output Power at 1dB Compression Point	P _{1dB}		dBm	40.0	40.5	-	
Power Gain at 1dB Compression Point	G _{1dB}	V _{DS} = 9V	dB	5.0	6.0	-	
Drain Current	I _{DS1}	f = 14.0 ~ 14.5 GHz	Α	-	4.0	5.0	1
Gain Flatness	ΔG		dB	-	-	±0.8	
Power Added Efficiency	η_{add}		%	-	21	-	
3rd Order Intermodulation Distortion	IM ₃	Note 1	dBc	-42	-45	-	DataShe
Drain Current	I _{DS2}	DataSheet4U.com	Α	-	4.0	5.0	1
Channel-Temperature Rise	ΔT_{ch}	V _{DS} x I _{DS} x R _{th (c-c)}	°C	-	-	90	1

Note 1: 2-tone Test Pout, Po = 29.0 dBm Single Carrier Level.

Electrical Characteristics ($T_a = 25^{\circ}C$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max.
Transconductance	gm	V _{DS} = 3V I _{DS} = 4.8A	mS	-	2800	-
Pinch-off Voltage	V _{GSoff}	V _{DS} = 3V I _{DS} = 145 mA	v	-2.0	-3.5	-5.0
Saturated Drain Current	IDSS	V _{DS} = 3V V _{GS} = 0V	А	-	10.0	11.5
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} = -145 μA	V	-5	-	-
Thermal Resistance	R _{th (c-c)}	Channel to Case	°C/W	-	2.0	2.5

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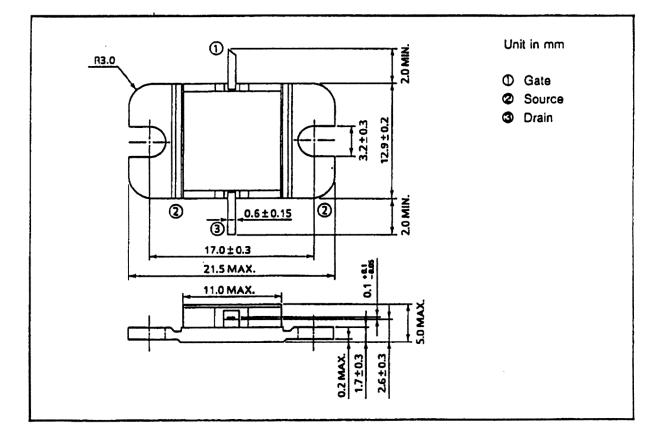
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Absolute Maximum Ratings (T_a = 25°C)

Characteristic	Symbol	Unit	Rating
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	11.5
Total Power Dissipation ($T_c = 25^{\circ}C$)	P _T	W	60
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65 ~ 175

Package Outline (2-11C1B)



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Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

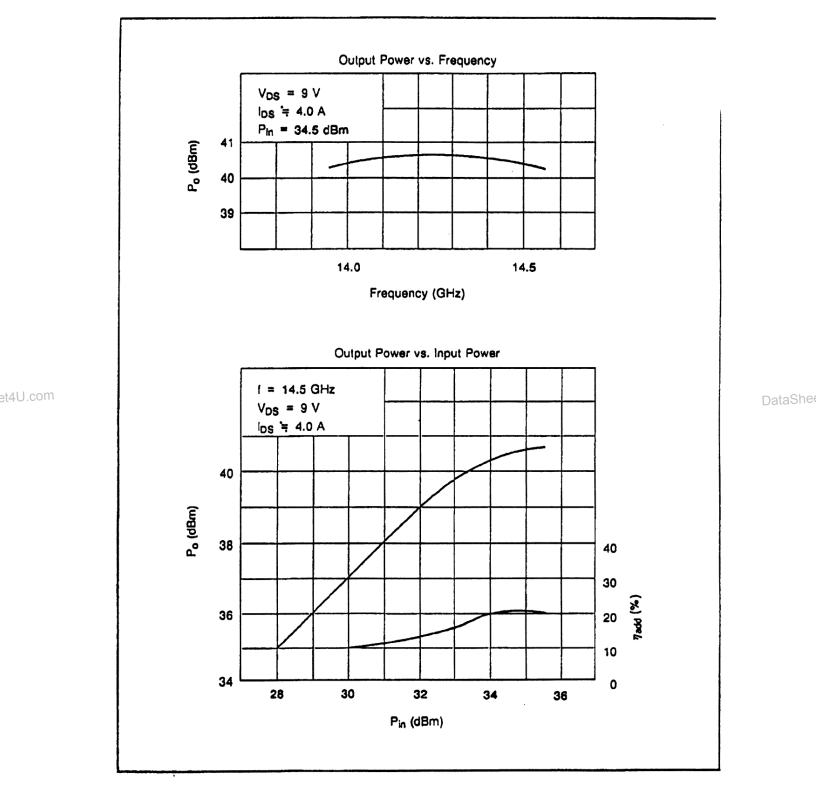
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RF Performances



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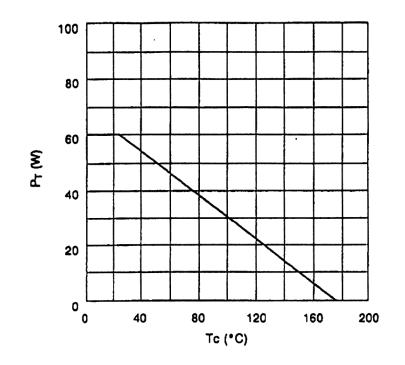
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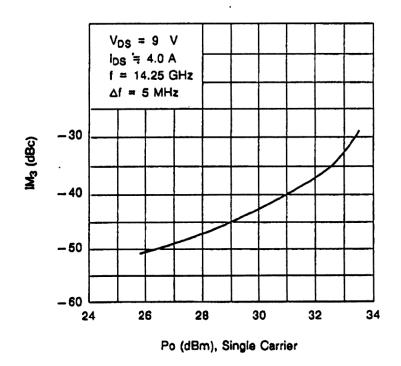
Power Dissipation vs. Case Temperature

IM₃ vs. Output Power Characteristics



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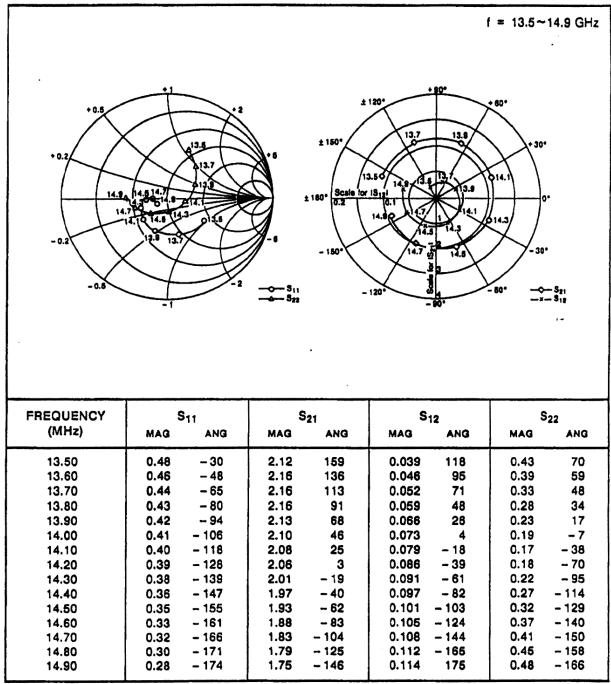
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